# ST1200C...KP Series

**Vishay Semiconductors** 

RoHS

COMPLIANT



## **Phase Control Thyristors** (Stud Version), 1650 A



### **FEATURES**

- · Center amplifying gate
- · Metal case with ceramic insulator
- International standard case A-24 (K-PUK)
- High profile hockey PUK
- Designed and qualified for industrial level
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912

### **TYPICAL APPLICATIONS**

- DC motor controls
- · Controlled DC power supplies
- AC controllers

PRODUCT SUMMARY	
I <sub>T(AV)</sub>	1650 A

MAJOR RATINGS AND CHARACTERISTICS								
PARAMETER	TEST CONDITIONS	VALUES	UNITS					
		1650	A					
I <sub>T(AV)</sub>	T <sub>hs</sub>	55	°C					
1		3080	A					
I <sub>T(RMS)</sub>	T <sub>hs</sub>	25	°C					
	50 Hz	30 500	•					
ITSM	60 Hz	32 000	A					
l <sup>2</sup> t	50 Hz	4651	kA <sup>2</sup> s					
I-t	60 Hz	4250	KA <sup>2</sup> S					
V <sub>DRM</sub> /V <sub>RRM</sub>		1200 to 2000	V					
tq	Typical	200	μs					
TJ		- 40 to 125	°C					

### **ELECTRICAL SPECIFICATIONS**

VOLTAGE RATINGS									
TYPE NUMBER	VOLTAGE CODE	V <sub>DRM</sub> /V <sub>RRM</sub> , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	$I_{DRM}/I_{RRM}$ MAXIMUM AT T <sub>J</sub> = T <sub>J</sub> MAXIMUM mA					
	12	1200	1300						
	14	1400	1500						
ST1200CK	16	1600	1700	100					
	18	1800	1900						
	20	2000	2100						

Revision: 27-Mar-13

Document Number: 94394

For technical questions within your region: DiodesAmericas@vishay.com, DiodesAsia@vishay.com, DiodesEurope@vishay.com THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000

## ST1200C..KP Series



Vishay Semiconductors

ABSOLUTE MAXIMUM RATING	5						
PARAMETER	SYMBOL		TEST CON	IDITIONS	VALUES	UNITS	
Maximum average on-state current	L	180° conduction, half sine wave		1650 (700)	А		
at heatsink temperature	I <sub>T(AV)</sub>	double side	(single side) co	oled	55 (85)	°C	
Maximum RMS on-state current	I <sub>T(RMS)</sub>	DC at 25 °C	heatsink tempe	erature double side cooled	3080		
		t = 10 ms	No voltage		30 500		
Maximum peak, one-cycle		t = 8.3 ms	reapplied		32 000	А	
non-repetitive surge current	I <sub>TSM</sub>	t = 10 ms	100 % V <sub>RRM</sub>		25 700		
		t = 8.3 ms	reapplied	Sinusoidal half wave,	26 900		
		t = 10 ms	No voltage	initial T <sub>J</sub> = T <sub>J</sub> maximum	4651	kA <sup>2</sup> s	
	l <sup>2</sup> t	t = 8.3 ms	reapplied		4250		
Maximum I <sup>2</sup> t for fusing	1 <del>-</del> t	t = 10 ms	100 % V <sub>RRM</sub>		3300		
		t = 8.3 ms	reapplied		3000	1	
Maximum I <sup>2</sup> $\sqrt{t}$ for fusing	l²√t	t = 0.1 ms te	o 10 ms, no volt	age reapplied	46 510	kA²√s	
Low level value of threshold voltage	V <sub>T(TO)1</sub>	(16.7 % x π	$x I_{T(AV)} < I < \pi x$	$I_{T(AV)}$ ), $T_J = T_J$ maximum	0.91	v	
High level value of threshold voltage	V <sub>T(TO)2</sub>	$(I > \pi \times I_{T(AV)})$	$(I > \pi \times I_{T(AV)}), T_J = T_J maximum$			v	
Low level value of on-state slope resistance	r <sub>t1</sub>	(16.7 % x $\pi$ x $I_{T(AV)} < I < \pi$ x $I_{T(AV)}$ ), $T_J = T_J$ maximum			0.21	mΩ	
High level value of on-state slope resistance	r <sub>t2</sub>	$(I > \pi x I_{T(AV)}), T_J = T_J maximum$		0.19	1115.2		
Maximum on-state voltage	V <sub>TM</sub>	$I_{pk} = 4000 \text{ A}, T_J = T_J \text{ maximum, } t_p = 10 \text{ ms sine pulse}$		1.73	V		
Maximum holding current	Ι <sub>Η</sub>	T 05 °C	$T_J = 25 \text{ °C}$ , anode supply 12 V resistive load		600		
Typical latching current	١L	$I_{\rm J} = 25^{-1}$ C,	anoue supply 1		1000	mA	

SWITCHING							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Maximum non-repetitive rate of rise of turned-on current	dl/dt	Gate drive 20 V, 20 $\Omega,t_r \leq 1~\mu s$ $T_J$ = $T_J$ maximum, anode voltage $\leq 80~\%~V_{DRM}$	1000	A∕µs			
Typical delay time	t <sub>d</sub>	Gate current 1 A, dl <sub>g</sub> /dt = 1 A/ $\mu$ s V <sub>d</sub> = 0.67 % V <sub>DRM</sub> , T <sub>J</sub> = 25 °C	1.9				
Typical turn-off time	tq	$I_{TM}$ = 550 A, $T_J$ = $T_J$ maximum, dl/dt = 40 A/µs, $V_R$ = 50 V, dV/dt = 20 V/µs, gate 0 V 100 $\Omega,$ $t_p$ = 500 µs	200	μs			

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum linear to 80 % rated $V_{DRM}$	500	V/µs
Maximum peak reverse and off-state leakage current	I <sub>RRM</sub> , I <sub>DRM</sub>	$T_J = T_J$ maximum, rated $V_{DRM}/V_{RRM}$ applied	100	mA

For technical questions within your region: DiodesAmericas@vishay.com, DiodesAsia@vishay.com, DiodesEurope@vishay.com THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000



### **Vishay Semiconductors**

TRIGGERING							
PARAMETER	SYMBOL	те	TEAT CONDITIONS			UNITS	
PARAMETER	STIVIDUL	TEST CONDITIONS		TYP.	MAX.	UNITS	
Maximum peak gate power	P <sub>GM</sub>	$T_J = T_J$ maximum,	$t_p \le 5 ms$	1	6	w	
Maximum average gate power	P <sub>G(AV)</sub>	$T_J = T_J$ maximum,	f = 50 Hz, d% = 50	;	3	vv	
Maximum peak positive gate current	I <sub>GM</sub>			3	.0	А	
Maximum peak positive gate voltage	$+ V_{GM}$	$T_J = T_J$ maximum,	$t_p \le 5 \text{ ms}$	2	0	V	
Maximum peak negative gate voltage	- V <sub>GM</sub>			5.0		v	
		T <sub>J</sub> = - 40 °C		200	-	mA	
DC gate current required to trigger	I <sub>GT</sub>	T <sub>J</sub> = 25 °C		100	200		
		T <sub>J</sub> = 125 °C	Maximum required gate trigger/ current/voltage are the lowest	50	-		
		T <sub>J</sub> = - 40 °C	value which will trigger all units 12 V anode to cathode applied	1.4	-		
DC gate voltage required to trigger	V <sub>GT</sub>	T <sub>J</sub> = 25 °C	12 V anode to cathode applied	1.1	3.0	V	
		T <sub>J</sub> = 125 °C		0.9	-		
DC gate current not to trigger	I <sub>GD</sub>	T. T. movimum	Maximum gate current/voltage not to trigger is the maximum	10		mA	
DC gate voltage not to trigger	V <sub>GD</sub>	$T_J = T_J maximum$	value which will not trigger any unit with rated V <sub>DRM</sub> anode to cathode applied	0.25		V	

THERMAL AND MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Maximum operating junction temperature range	TJ		- 40 to 125	°C			
Maximum storage temperature range	T <sub>Stg</sub>		- 40 to 150				
Maximum thermal resistance,	Б	DC operation single side cooled	0.0.42	K/W			
junction to heatsink	R <sub>thJ-hs</sub>	DC operation double side cooled	0.021				
Maximum thermal resistance,	Б	DC operation single side cooled	0.006				
case to heatsink	R <sub>thC-hs</sub>	DC operation double side cooled	0.003				
Mounting force, ± 10 %			24 500 (2500)	N (kg)			
Approximate weight			425	g			
Case style		See dimensions - link at the end of datasheet A-24 (K-P		(-PUK)			

CONDUCTION ANGLE	SINUSOIDAL CONDUCTION		RECTANGULAR	R CONDUCTION	TEST CONDITIONS	UNITS		
CONDUCTION ANGLE	SINGLE SIDE	DOUBLE SIDE	SINGLE SIDE	DOUBLE SIDE	TEST CONDITIONS			
180°	0.003	0.003	0.002	0.002				
120°	0.004	0.004	0.004	0.004				
90°	0.005	0.005	0.005	0.005	$T_J = T_J maximum$	K/W		
60°	0.007	0.007	0.007	0.007				
30°	0.012	0.012	0.012	0.012				

Note

• The table above shows the increment of thermal resistance R<sub>thJC</sub> when devices operate at different conduction angles than DC



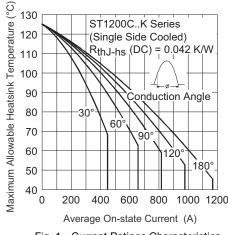
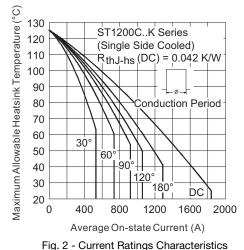
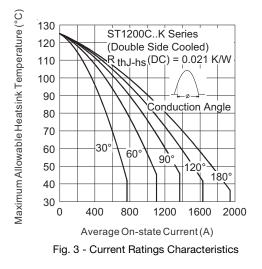
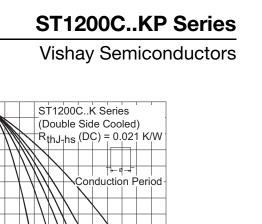


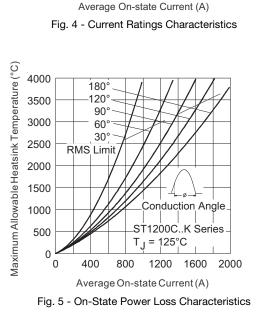
Fig. 1 - Current Ratings Characteristics



rig. 2 - Current Hatings Characteristics





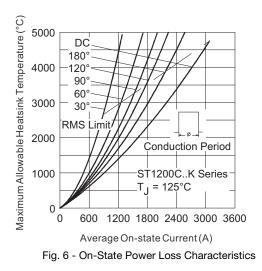


Maximum Allowable Heatsink Temperature (°C)

60°-1 

1800 2400 3000

DC



Revision: 27-Mar-13

Document Number: 94394

For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>

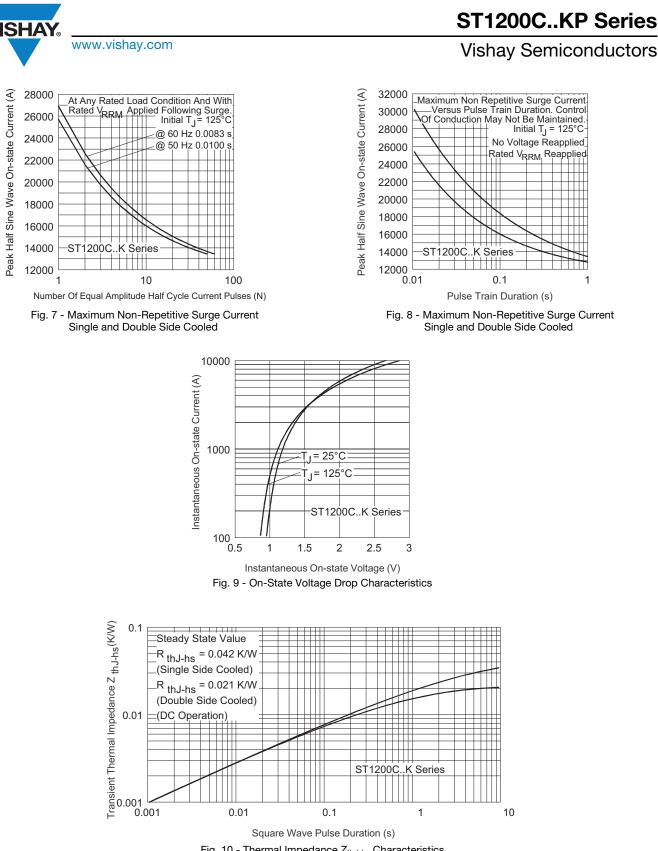


Fig. 10 - Thermal Impedance ZthJ-hs Characteristics

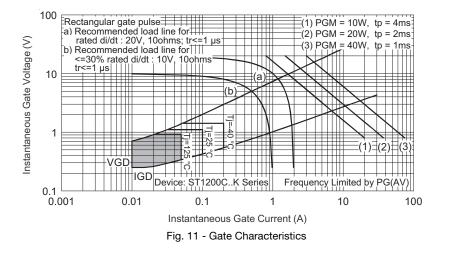
5

Document Number: 94394

For technical questions within your region: DiodesAmericas@vishay.com, DiodesAsia@vishay.com, DiodesEurope@vishay.com THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000

## ST1200C..KP Series

### **Vishay Semiconductors**



#### **ORDERING INFORMATION TABLE**

www.vishay.com

Device code	ST	120	0	С	20	К	1	-	Ρ	
	1	2	3	4	5	6	7	8	9	I
	1 -	- Thy	ristor							
	2 -	- Ess	ential pa	art numt	ber					
	3 -	0 =	Conver	ter grade	Э					
	4 -	- C =	Cerami	c PUK						
	5 -	- Volt	age coo	le: Code	e x 100 :	= V <sub>RRM</sub>	(see Vo	oltage R	atings t	able)
	6 -	- K =	PUK ca	ise A-24	(K-PUł	<)				
	7 -	0 =	Eyelet t	erminals	s (gate a	and aux	iliary ca	thode u	nsolder	ed leads)
		1 =	Fast-on	termina	lls (gate	and au	xiliary c	athode	unsolde	ered leads)
		2 =	Eyelet t	erminals	s (gate a	and aux	iliary ca	thode s	oldered	leads)
		3 =	Fast-on	termina	ls (gate	and au	xiliary c	athode	soldere	d leads)
	8 -	Crit	ical dV/o	dt: • Noi • L =	ne = 500 1000 V	• •			tion)	
	9 -	P =	Lead (F	b)-free						

LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95081			



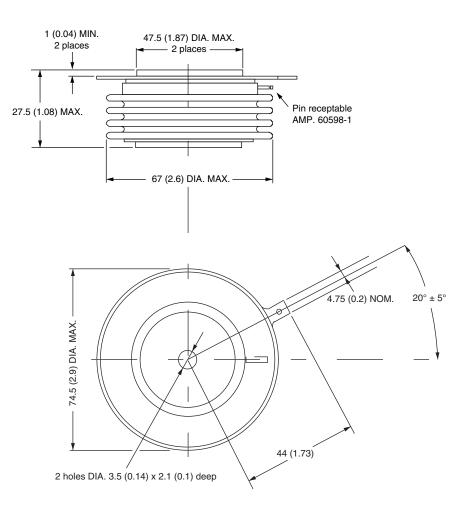
### **Outline Dimensions**

**Vishay Semiconductors** 

## A-24 (K-PUK)

#### **DIMENSIONS** in millimeters (inches)

Creepage distance: 28.88 (1.137) minimum Strike distance: 17.99 (0.708) minimum



Quote between upper and lower pole pieces has to be considered after application of mounting force (see thermal and mechanical specification)



Vishay

## Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and/or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

## **Material Category Policy**

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as RoHS-Compliant fulfill the definitions and restrictions defined under Directive 2011/65/EU of The European Parliament and of the Council of June 8, 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (EEE) - recast, unless otherwise specified as non-compliant.

Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as Halogen-Free follow Halogen-Free requirements as per JEDEC JS709A standards. Please note that some Vishay documentation may still make reference to the IEC 61249-2-21 definition. We confirm that all the products identified as being compliant to IEC 61249-2-21 conform to JEDEC JS709A standards.